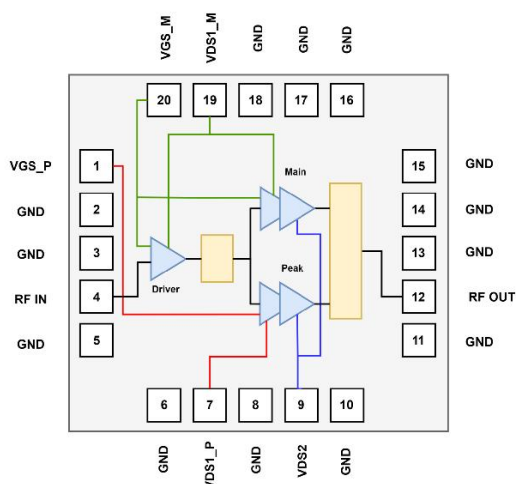


## Description

The H8G0810M06P is a LDMOS MMIC Integrated Asymmetrical Doherty based on 2-Stage with 6W saturated output power covering frequency range from 860 - 960 MHz.

The amplifier is 50  $\Omega$  Input/Output matched with a small compact footprint 7x7 mm which makes it ideal for integration.

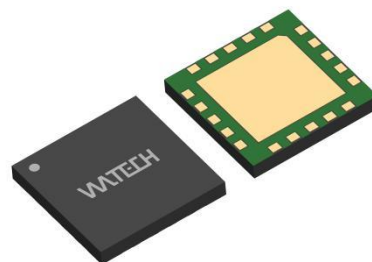
## Block Diagram



H8G0810M06P Block Diagram

## Applications

- 3GPP 5G NR FR1 n5/8/18/26 and 4G-LTE band B5/8/18/26
- Power Amplifier for Small Cells
- Driver Amplifier for Micro and Macro Base Stations
- Active Antenna Array for 5G mMIMO
- Repeaters/DAS
- Mobile Infrastructure



20 Pin LGA 7x7 mm Plastic Package

## Features

- Operating Frequency Range: 860 - 960 MHz
- Operating Drain Voltage: +28V
- Saturation Output Power: 6W
- Power Average: 0.63W
- 50  $\Omega$  Input/Output matched
- Integrated Input Divider
- Integrated Output Combiner
- Integrated Asymmetrical Doherty Final Stage
- High Efficiency: 45.1%@860MHz, WCDMA
- High Gain: 18.7dB@860MHz, WCDMA
- Small footprint package: LGA 7x7 mm

## Ordering Information

Part Number	Description
H8G0810M06P	Reel Package
H8G0810M06PEVB	860 - 960 MHz EVB

#### RF Characteristics (Pulsed CW)

Freq (MHz)	P3dB (dBm)	Gain (dB)	Eff (%)	IRL (dB)
860	37.2	19.0	46.1	12.4
910	37.2	19.2	50.8	19.7
960	37.7	18.8	48.5	19.0

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 18mA$ ,  $V_{gsp} = V_{gsm} - 0.72V$ , Pulse Width = 100us, Duty Cycle = 10% test on HOTLO Application Board

#### RF Characteristics (WCDMA)

Freq (MHz)	Gain (dB)	Eff (%)	IRL (dB)	ACPR* @5MHz (dBc)
860	18.7	45.1	12.7	-30.3
910	18.7	46.7	19.8	-31.3
960	18.6	45.2	19.3	-37.2

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 18mA$ ,  $V_{gsp} = V_{gsm} - 0.72V$ ,  $PAVG = 28 dBm$   
1C-WCDMA 5MHz Signal, 7.6 dB PAR @ 0.01% CCDF test on HOTLO Application Board

\*Uncorrected DPD

#### Absolute Maximum Ratings

Parameter	Range/Value	Unit
Drain voltage ( $V_{DSS}$ )	-0.5 to +65	V
Gate voltage ( $V_{GS}$ )	-5 to +10	V
Drain voltage ( $V_{DD}$ )	0 to +28	V
Storage Temperature ( $T_{STG}$ )	-55 to +150	°C
Case Temperature ( $T_C$ )	-40 to +125	°C
Junction Temperature ( $T_J$ )	-40 to +175	°C

#### DC Characteristics

Parameter	Conditions	Min	Typ	Max	Unit
Breakdown Voltage $V_{(BR)DSS}$	$V_{gs}=0V, I_{ds}=100\mu A$	65	-	-	V
Gate-Source Threshold Voltage $V_{GS(th)}$	$V_{gs}=V_{ds}, I_{ds}=5.2\mu A$	1.2	-	1.6	V
Drain Leakage Current $I_{DSS}$	$V_{gs}=0V, V_{ds}=28V$	-	-	0.5	$\mu A$
Gate Leakage Current $I_{GSS}$	$V_{gs}=5V, V_{ds}=0V$	-	-	0.05	$\mu A$

#### RF Characteristics (Pulsed CW)

Parameter	Freq (MHz)	Min	Typ.	Max	Unit
P3dB	910	36	37.2	-	dBm

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 18mA$ ,  $V_{gsp} = V_{gsm}-0.72V$ , Pulse Width = 100us, Duty Cycle = 10% test on HOTLO Production Board

#### RF Characteristics (WCDMA)

Parameter	Conditions	Min	Typ.	Max	Unit
Frequency	910				MHz
Gain	$PAVG = 28\text{ dBm}$	18.5	18.7	19	dB
Eff	$PAVG = 28\text{ dBm}$	40	46.7	-	%
IRL	$PAVG = 28\text{ dBm}$	10	19.8	-	dB
ACPR@5MHz*	$PAVG = 28\text{ dBm}$	-	-31.3	-26	dBc

Test conditions unless otherwise noted: 25 °C,  $V_{DD}=+28V_{dc}$ ,  $I_{DQ} = 18mA$ ,  $V_{gsp} = V_{gsm}-0.72V$ , 1C-WCDMA 5MHz Signal, 7.6 dB PAR @ 0.01% CCDF test on HOTLO Production Board

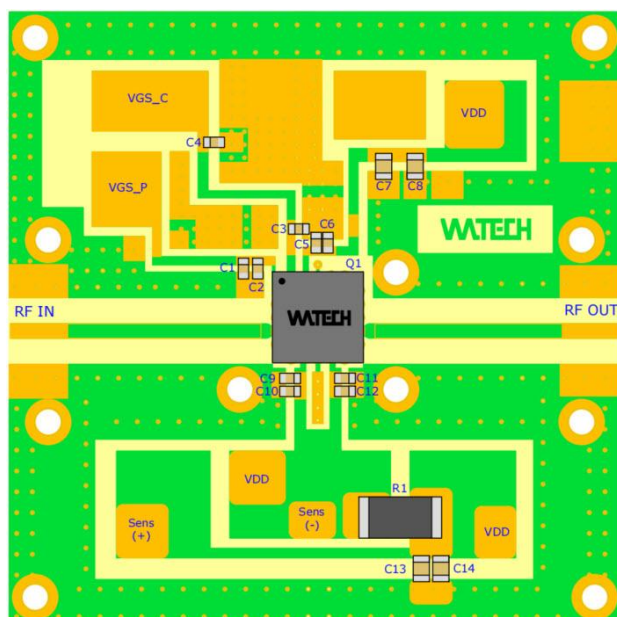
\*Uncorrected DPD

#### Load Mismatch Test

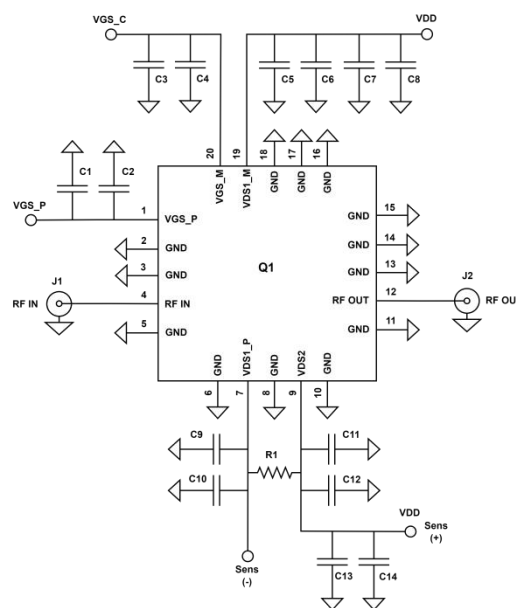
Condition	Test Result
CW, $V_{DD}=+28V_{dc}$ , $I_{DQ} = 35\text{ mA}$ , $V_{gsp}=V_{gsm}-0.72V$ , $PAVG = 37\text{ dBm}$ Frequency 860 to 960 MHz, test on HOTLO Application Board	No Device Degradation

#### Thermal Information

Parameter	Condition	Value (Typ)	Unit
Thermal Resistance Junction to Case ( $R_{TH}$ )	$T_{CASE}= 90^{\circ}C$ , 1C-WCDMA 5MHz Signal, 7.6 dB PAR, $PAVG = 28\text{ dBm}$	11	$^{\circ}C / W$



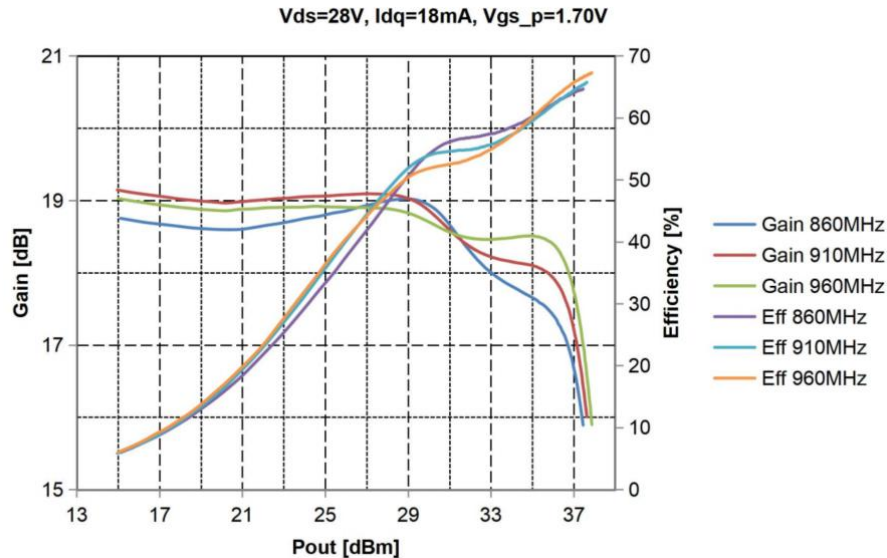
EVb Layout



EVb Schematic

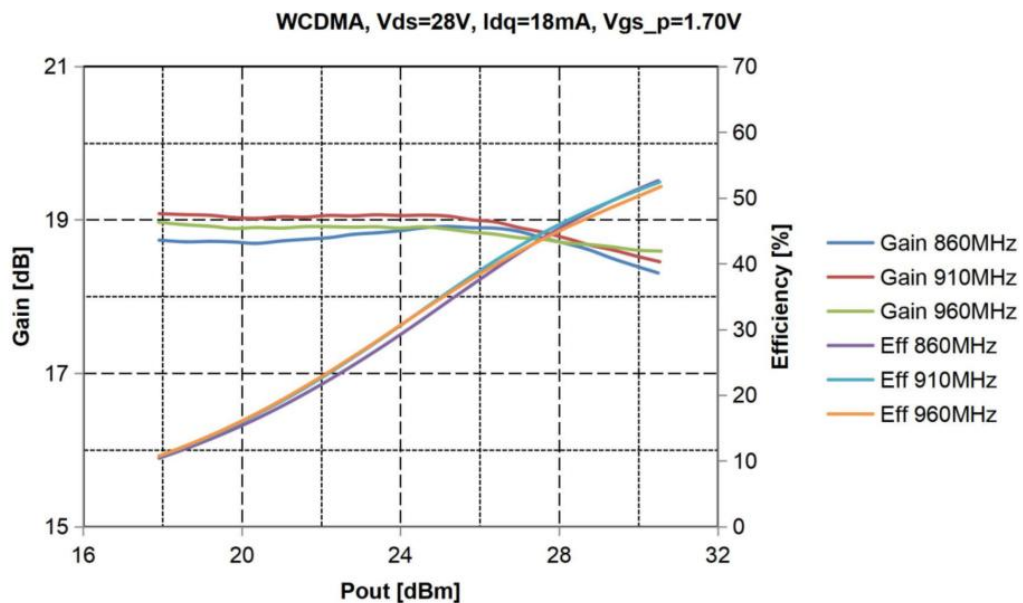
### Bill of Materials (BoM) - H8G0810M06P 860 - 960 MHz Reference Design

Reference	Value	Description	Manufacturer	P/N
Q1	-	6W, 860 - 960 MHz LDMOS MMIC PA	Holto	H8G0810M06P
C7,C8, C13,C14	1uF $\pm$ 10%, 0805	Multi-Layer Ceramic Capacitor	Murata	GRM219R7YA105KA12
C1-C6, C9 - C12	1uF $\pm$ 10%, 0603	Multi-Layer Ceramic Capacitor	Murata	GCM188R71E105KA64D
R1	100m $\Omega$ /1W, 0.1%	High-Precision Resistor	Vishay	Y44870R10000B0R
PCB	<ul style="list-style-type: none"> <li>Rogers 4350B, er = 3.66; Thickness= 20 mil (0.508 mm); Thickness copper plating = 35 <math>\mu</math>m (1oz)</li> <li>Soldered on a 47x47x10 mm Copper Base-Plate</li> </ul>			



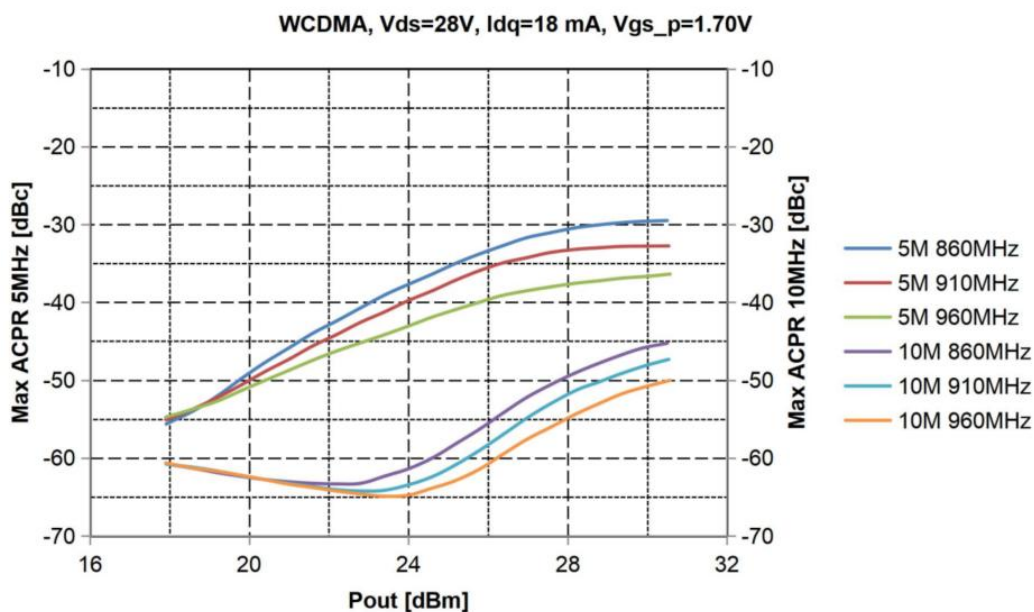
**Pulsed CW, Gain and Efficiency vs Pout**

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ = 18mA, Vgsp = Vgsm-0.72V, Pulse Width = 100 us, Duty Cycle = 10% test on HOTLO Application Board



**WCDMA, Gain and Efficiency vs Pout**

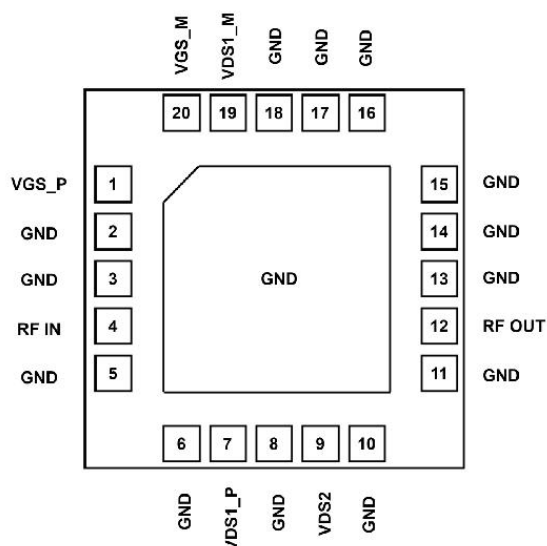
Test conditions unless otherwise noted: 25 °C, VDD=+28Vdc, IDQ = 18mA, Vgsp = Vgsm-0.72V, 1C-WCDMA 5MHz Signal, 7.6 dB PAR @ 0.01% CCDF test on HOTLO Application Board



WCDMA, ACPR\_5MHz, ACPR\_10MHz vs Pout

Test conditions unless otherwise noted: 25 °C,  $V_{DD}=+28V_{dc}$ ,  $I_{DQ} = 18mA$ ,  $V_{gsp} = V_{gsm}-0.72V$ , 1C-WCDMA 5MHz Signal, 7.6 dB PAR @ 0.01% CCDF test on HOTLO Application Board

### Pin Configuration and Description



17	GND	Ground
18	GND	Ground
19	VDS1_M	Drain-Source Voltage Main Driver
20	VGS_M	Gate-Source Voltage Main

Pinout Device Configuration

Pin Number	Label	Description
1	VGS_P	Gate-Source Voltage Peak
2	GND	Ground
3	GND	Ground
4	RFIN	RF Input
5	GND	Ground
6	GND	Ground
7	VDS1_P	Drain-Source Voltage Peak Driver
8	GND	Ground
9	VDS2	Drain-Source Voltage Final Stage
10	GND	Ground
11	GND	Ground
12	RFOUT	RF Output
13	GND	Ground
14	GND	Ground
15	GND	Ground
16	GND	Ground

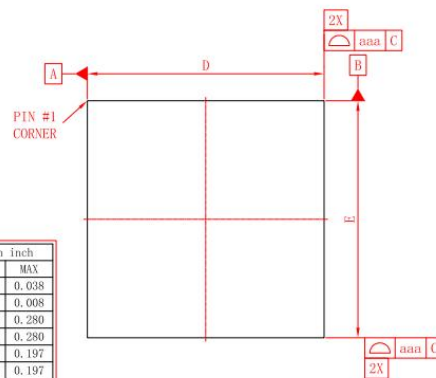




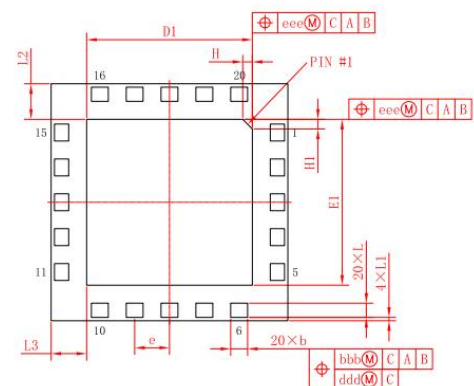
- Line1 (fixed): Device name in W/O
- Line2 (unfixed): Marking Lot No in W/O (Sample: E596-20140001)
- Line3 (unfixed): Date Code + JY
- This Marking SPEC only stipulates the content of Marking. For marking requirements such as font and size, please refer to the latest version of "Holto Product Printing Specification"

#### Marking

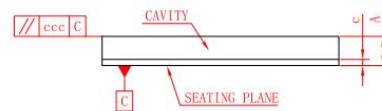
symbol	Dimension in mm			Dimension in inch		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.760	0.860	0.960	0.030	0.034	0.038
c	0.150	0.180	0.210	0.006	0.007	0.008
D	6.900	7.000	7.100	0.272	0.276	0.280
E	6.900	7.000	7.100	0.272	0.276	0.280
D1	4.800	4.900	5.000	0.189	0.193	0.197
E1	4.800	4.900	5.000	0.189	0.193	0.197
H	---	0.286	---	---	0.011	---
H1	---	0.286	---	---	0.011	---
L	0.370	0.420	0.470	0.015	0.017	0.019
L1	0.025	0.100	0.175	0.001	0.004	0.007
L2	0.975	1.050	1.125	0.038	0.041	0.044
L3	0.975	1.050	1.125	0.038	0.041	0.044
e	---	1.030	---	---	0.041	---
b	0.450	0.500	0.550	0.018	0.020	0.022
aaa	---	0.150	---	---	0.006	---
bbb	---	0.150	---	---	0.006	---
ccc	---	0.100	---	---	0.004	---
ddd	---	0.080	---	---	0.003	---
eee	---	0.150	---	---	0.006	---



Top View



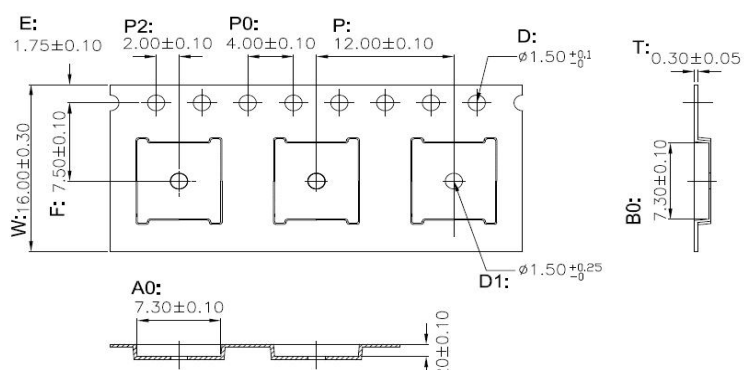
Bottom View



Side View

#### Package Dimensions






### Notes:

1. Carrier tape color: BLACK.
2. Carrier material :PS (Polystyrene).
3. ESD surface resistivity  $< 1 \times 10^{11} \Omega/\text{square}$  per EIA, JEDEC TNR specification.
4. Heat deflection temperature for Tape & Reel material: 62°C
5. Vicat softening temperature (10N) for Tape & Reel material: 95°C
6. Dimension is millimeter.

### Tape & Reel Packaging Descriptions

## Handling Precautions

Parameter	Grade
Moisture Sensitivity Level MSL	3

Parameter	Rating	Standard	
ESD – Human Body Model (HBM)	Class 1B	JESD22-A114	
ESD – Human Body Model (MM)	Class A	EIA/JESD22-A115	
ESD – Charged Device Model (CDM)	Class III	JESD22-C101	

## RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

## Datasheet Status

Document status	Product status	Definition
Objective Datasheet	Design simulation	Product objective specification
Preliminary Datasheet	Customer sample	Engineering samples and first test results
Product Datasheet	Mass production	Final product specification

Acronym	Definition
LDMOS	Laterally-Diffused Metal-Oxide Semiconductor
CW	Continuous Waveform
VSWR	Voltage Standing Wave Ratio

### Revision history

Document ID	Datasheet Status	Release Date	Revision Version
Rev 2.3	Product	May 2020	Product release
Rev 2.4	Product	March 2023	New format based on English version datasheet
Rev 2.5	Product	April 2024	Update thermal Information

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For the latest specifications, additional product information, worldwide sales and distribution locations and information about HOTLO:

- Web: [www.andesource.com](http://www.andesource.com)
- Email: [andehk@andesource.com](mailto:andehk@andesource.com)

For technical questions and application information:

- Email: [andetech@andesource.com](mailto:andetech@andesource.com)

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